

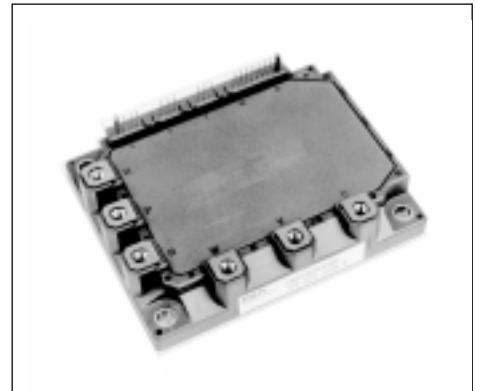
6MBP75RA120

IGBT-IPM R series

1200V / 75A 6 in one-package

Features

- Temperature protection provided by directly detecting the junction temperature of the IGBTs
- Low power loss and soft switching
- Compatible with existing IPM-N series packages
- High performance and high reliability IGBT with overheating protection
- Higher reliability because of a big decrease in number of parts in built-in control circuit



Maximum ratings and characteristics

- Absolute maximum ratings(at $T_c=25^{\circ}\text{C}$ unless otherwise specified)

Item			Symbol	Rating		Unit
				Min.	Max.	
DC bus voltage			V _{DC}	0	900	V
DC bus voltage (surge)			V _{DC(surge)}	0	1000	V
DC bus voltage (short operating)			V _{SC}	200	800	V
Collector-Emitter voltage			V _{CES}	0	1200	V
INV	Collector current	DC	I _C	-	75	A
		1ms	I _{CP}	-	150	A
		DC	-I _C	-	75	A
	Collector power dissipation		One transistor	P _C	-	500
Junction temperature			T _J	-	150	°C
Input voltage of power supply for Pre-Driver			V _{CC} *1	0	20	V
Input signal voltage			V _{in} *2	0	V _Z	V
Input signal current			I _{in}	-	1	mA
Alarm signal voltage			V _{ALM} *3	0	V _{CC}	V
Alarm signal current			I _{ALM} *4	-	15	mA
Storage temperature			T _{stg}	-40	125	°C
Operating case temperature			T _{op}	-20	100	°C
Isolating voltage (Case-Terminal)			V _{iso} *5	-	AC2.5	kV
Screw torque		Mounting (M5)		-	3.5 *6	N·m
		Terminal (M5)		-	3.5 *6	N·m

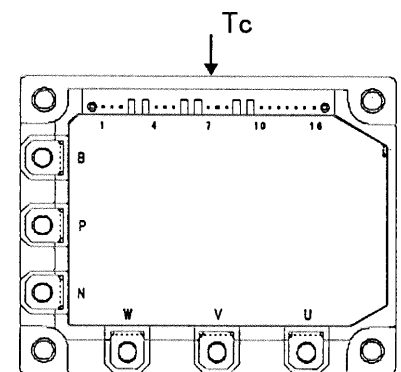


Fig.1 Measurement of case temperature

*1 Apply V_{CC} between terminal No. 3 and 1, 6 and 4, 9 and 7, 11 and 10.

*2 Apply V_{in} between terminal No. 2 and 1, 5 and 4, 8 and 7, 13,14,15 and 10.

*3 Apply V_{ALM} between terminal No. 16 and 10.

*4 Apply I_{ALM} to terminal No. 16.

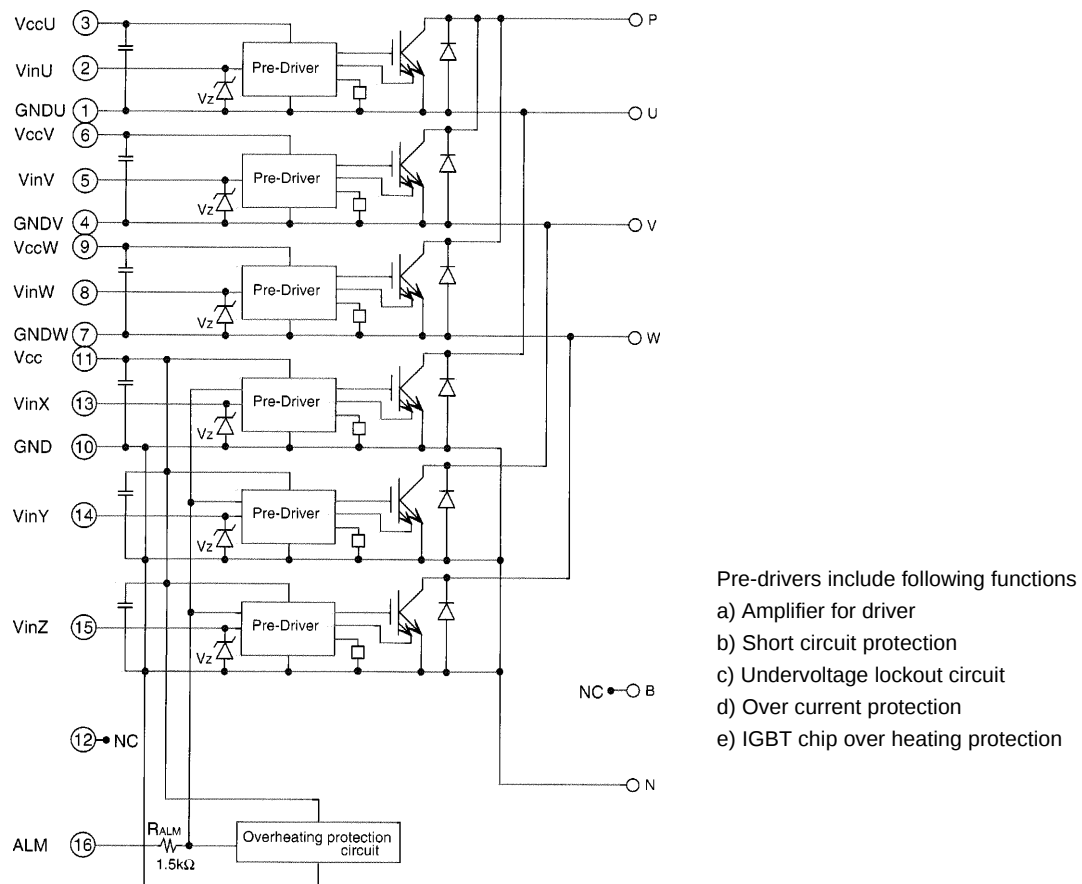
*5 50Hz/60Hz sine wave 1 minute.

*6 Recommendable Value : 2.5 to 3.0 N·m

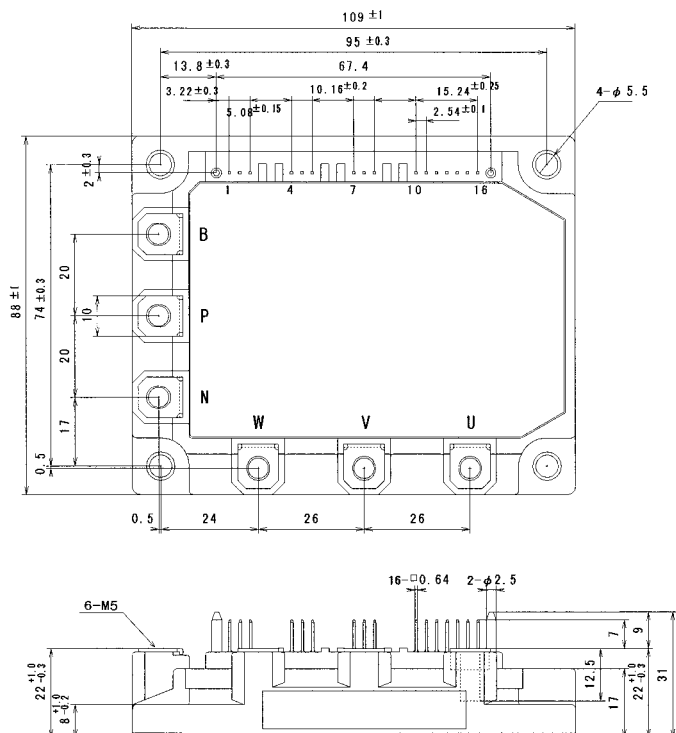
- Electrical characteristics of power circuit (at $T_c=T_J=25^{\circ}\text{C}$, $V_{CC}=15\text{V}$)

Item		Symbol	Condtion	Min.	Typ.	Max.	Unit
INV	Collector current at off signal input	ICES	VCE=1200V input terminal open	—	—	1.0	mA
	Collector-Emitter saturation voltage	VCE(sat)	Ic=75A	—	—	2.6	V
	Forward voltage of FWD	VF	-Ic=75A	—	—	3.0	V

■ Block diagram

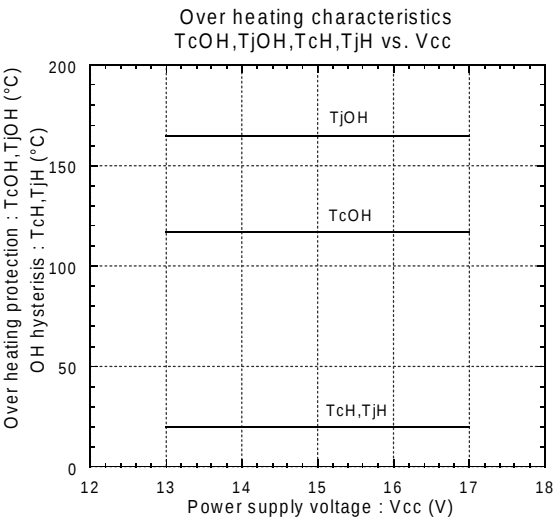
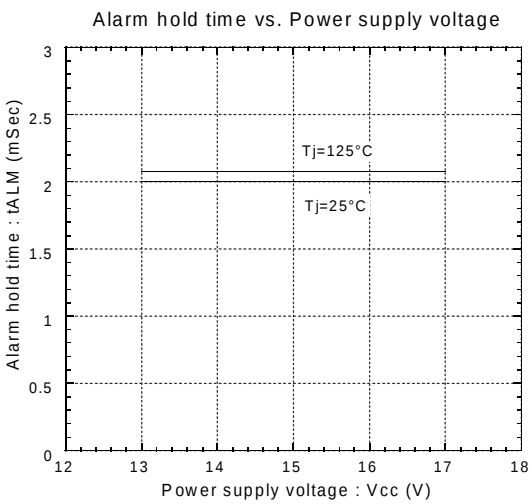
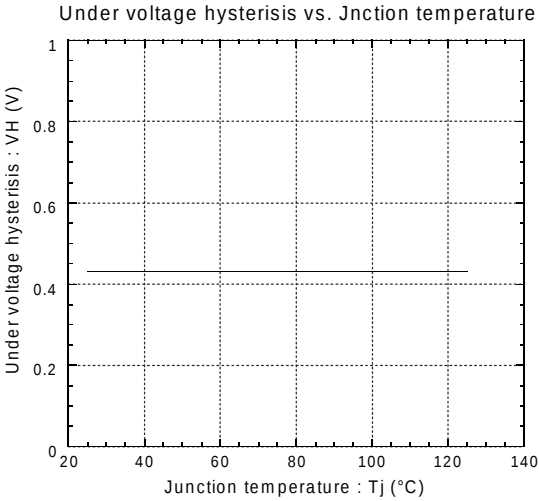
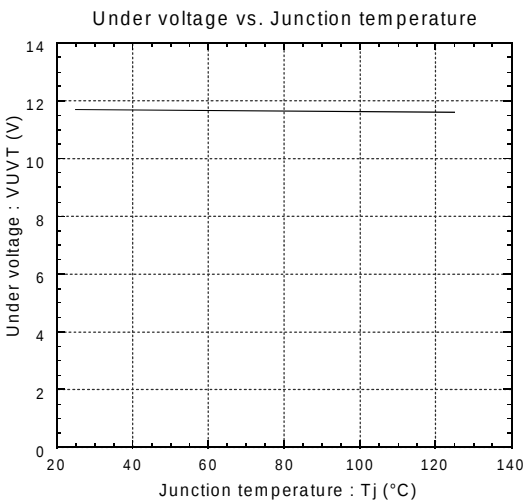
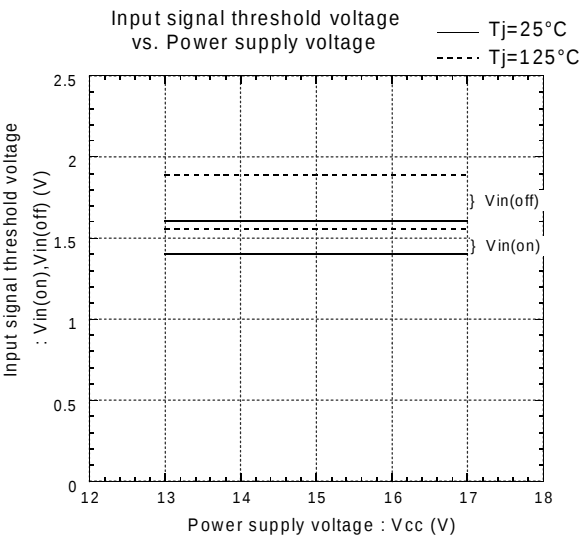
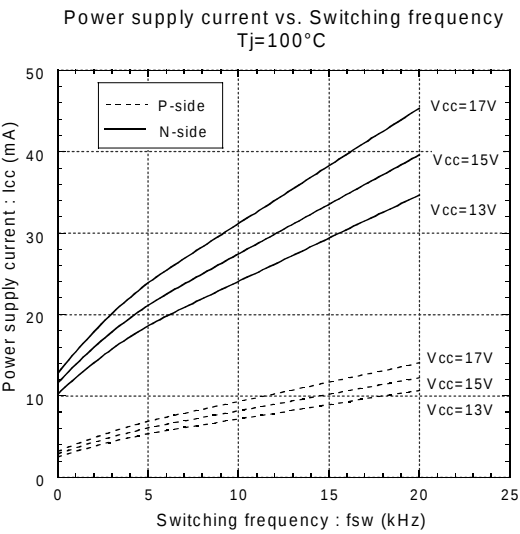


■ Outline drawings, mm



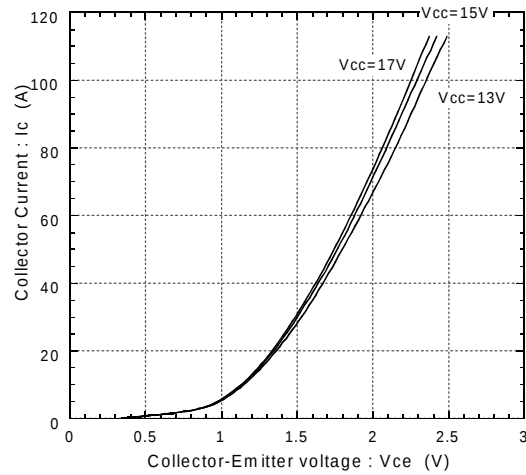
Characteristics (Representative)

Control Circuit

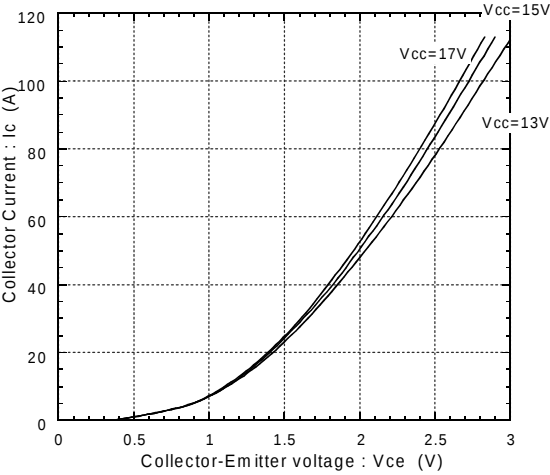


● Inverter

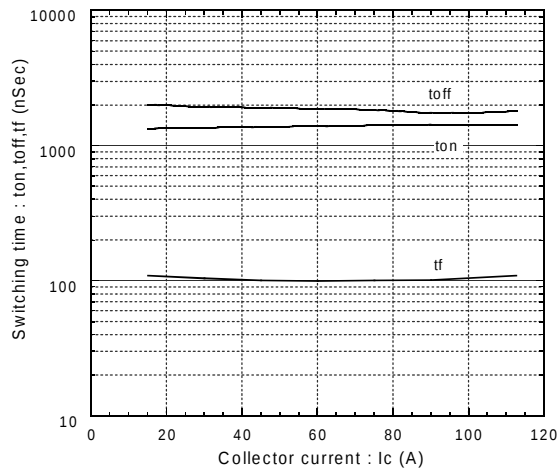
Collector current vs. Collector-Emitter voltage
 $T_j=25^{\circ}\text{C}$



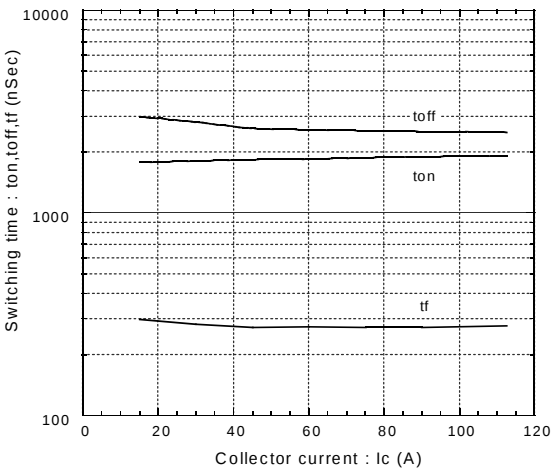
Collector current vs. Collector-Emitter voltage
 $T_j=125^{\circ}\text{C}$



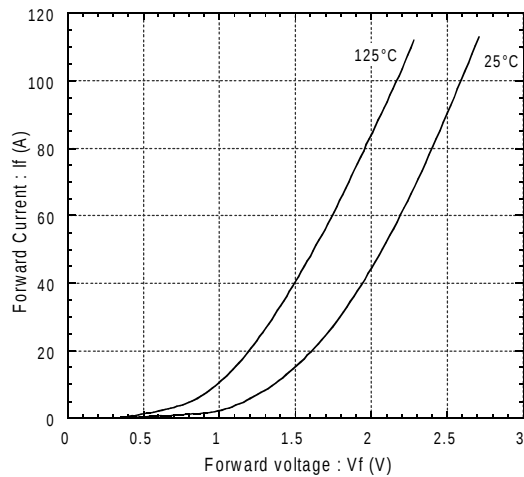
Switching time vs. Collector current
 $E_{dc}=600\text{V}, V_{cc}=15\text{V}, T_j=25^{\circ}\text{C}$



Switching time vs. Collector current
 $E_{dc}=600\text{V}, V_{cc}=15\text{V}, T_j=125^{\circ}\text{C}$



Forward current vs. Forward voltage



Reverse recovery characteristics
 t_{rr}, I_{rr} vs. I_F

